

AMENDMENTS TO THE CLAIMS

The following listing of claims is provided in accordance with 37 C.F.R. § 1.121.

1-34. (Canceled)

35. (Currently Amended) An integrated circuit comprising:
a stack comprising at least two semiconductor die, each of the semiconductor die
being coupled together by a first adhesive, the first adhesive being curable at a
first temperature; and
a substrate coupled to one of the at least two semiconductor die by a second adhesive,
the second adhesive being curable at a second temperature lower than the first
temperature; ~~wherein each die in the stack of at least two semiconductor die is
electrically functional.~~

36. (Canceled)

37. (Previously Presented) The integrated circuit, as set forth in claim 35, wherein the
topside surface area of one of the at least two semiconductor die is less than the topside
surface area of a second of the at least two semiconductor die.

38. (Previously Presented) An integrated circuit comprising:
a stack comprising at least two semiconductor die, each of the semiconductor die
being coupled together by a first adhesive, the first adhesive being curable at a
first temperature; and
a substrate coupled to one of the at least two semiconductor die by a second adhesive,
the second adhesive being curable at a second temperature lower than the first
temperature;
wherein the stack of at least two semiconductor die is configured such that the stack
comprises a shingle stack.

39. (Previously Presented) The integrated circuit, as set forth in claim 35, wherein at least
one of the at least two semiconductor die comprises a memory die.

40-44. (Canceled)

45. (Currently Amended) An integrated circuit comprising:

a stack of at least two semiconductor die, each of the die being coupled to an adjacent die in the stack by a respective layer of a first adhesive prior to the stack being coupled to a packaging substrate, wherein ~~each die in the stack of at least two semiconductor die is electrically functional~~ the first adhesive is curable at a first temperature; and

a second adhesive disposed on an outer side of the stack to facilitate coupling the stack with the packaging substrate, wherein the second adhesive is curable at a second temperature lower than the first temperature.

46. (Canceled)

47. (Original) The integrated circuit, as set forth in claim 45, wherein the topside surface area of one of the at least two semiconductor die is less than the topside surface area of a second of the at least two semiconductor die.

48. (Canceled)

49. (Original) The integrated circuit, as set forth in claim 45, wherein at least one of the at least two semiconductor die comprises a memory die.

50-65. (Canceled)

66. (Currently Amended) An integrated circuit package comprising:

a substrate; and

a die stack coupled to the substrate, wherein the die stack comprises at least two semiconductor die coupled together via a first adhesive that is curable at a first temperature and has been cured; and

a second adhesive disposed between the die stack and the substrate that is curable at a second temperature lower than the first temperature. ~~wherein the die stack is formed prior to being coupled to the substrate;~~

~~wherein the stack of at least two semiconductor die is configured such that the stack comprises a shingle stack.~~

67. (Currently Amended) The integrated circuit package, as set forth in claim ~~66~~ 63, wherein at least one of the at least two semiconductor die comprises a memory die.

68. (Currently Amended) An integrated circuit comprising:
a stack comprising at least two semiconductor die, each of the semiconductor die
being coupled together by a first adhesive, the first adhesive being curable at a
first temperature; and
a substrate coupled to one of the at least two semiconductor die by a second adhesive,
the second adhesive being curable at a second temperature lower than the first
temperature;
wherein each die in the stack of at least two die is successively thinner than the
previous die as the die approach the substrate.

69-70. (Canceled)